

Tentative Data

Insulated Gate Bi-Polar Transistor

Type T0600NC17A

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	1700	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	900	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I_C	DC collector current, IGBT	600	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1200	A
$I_{F(DC)}$	Continuous DC forward current, Diode	600	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	1200	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	2410	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	2650	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	1.85	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	3500	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 240nH.
- 4) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	2.35	2.65	$I_C = 600A, V_{GE} = 15V, T_j = 25^\circ C$	V
		-	3.0	3.3	$I_C = 600A, V_{GE} = 15V$	V
V_{T0}	Threshold voltage	-	-	1.22	Current range: 200A – 600A	V
r_T	Slope resistance	-	-	3.48		mΩ
$V_{GE(TH)}$	Gate threshold voltage	-	5	-	$V_E = V_{GE}, I_C = 20mA$	V
I_{CES}	Collector – emitter cut-off current	-	3.5	10	$V_{CE} = V_{CES}, V_{GE} = 0V$	mA
I_{GES}	Gate leakage current	-	-	±10	$V_{GE} = \pm 20V$	μA
C_{ies}	Input capacitance	-	47	-	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	nF
$t_{d(on)}$	Turn-on delay time	-	0.22	-	$I_C = 600A, V_{CE} = 900V, di/dt = 3000A/\mu s$ $V_{GE} = \pm 15V, L_s = 240nH$ $R_{g(ON)} = 3.3\Omega, R_{g(OFF)} = 24\Omega, C_{GE} = 75nF$ Integral diode used as freewheel diode (Note 3)	μs
$t_r(V)$	Rise time	-	0.8	-		μs
$Q_{g(on)}$	Turn-on gate charge	-	2.6	-		μC
E_{on}	Turn-on energy	-	0.29	-		J
$t_{d(off)}$	Turn-off delay time	-	2	-		μs
$t_f(I)$	Fall time	-	0.54	-		μs
$Q_{g(off)}$	Turn-off gate charge	-	1.5	-		μC
E_{off}	Turn-off energy	-	0.5	-		J
I_{SC}	Short circuit current	-	1500	-	$V_{GE} = +15V, V_{CC} = 900V, V_{CEmax} \leq V_{CES}, t_p \leq 10\mu s$	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V_F	Forward voltage	-	2.12	2.40	$I_F = 600A, T_j = 25^\circ C$	V
		-	2.24	2.55	$I_F = 600A$	V
V_{T0}	Threshold voltage	-	-	1.42	Current range 200A - 600A	V
r_T	Slope resistance	-	-	1.88		mΩ
I_{rm}	Peak reverse recovery current	-	300	-	$I_F = 600A, V_r = 900V, V_{GE} = -15V,$ $di/dt = 3000A/\mu s$	A
Q_{rr}	Recovered charge	-	175	-		μC
t_{rr}	Reverse recovery time, 50% chord	-	0.5	-		μs
E_r	Reverse recovery energy	-	0.12	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	54.1	Double side cooled	K/kW
		-	-	93	Collector side cooled	K/kW
		-	-	131	Emitter side cooled	K/kW
R_{thJK}	Thermal resistance junction to sink, Diode	-	-	125	Double side cooled	K/kW
		-	-	205	Cathode side cooled	K/kW
		-	-	319	Anode side cooled	K/kW
F	Mounting force	8	-	12	Note 2	kN
W_t	Weight	-	0.5	-		kg

Notes:-

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

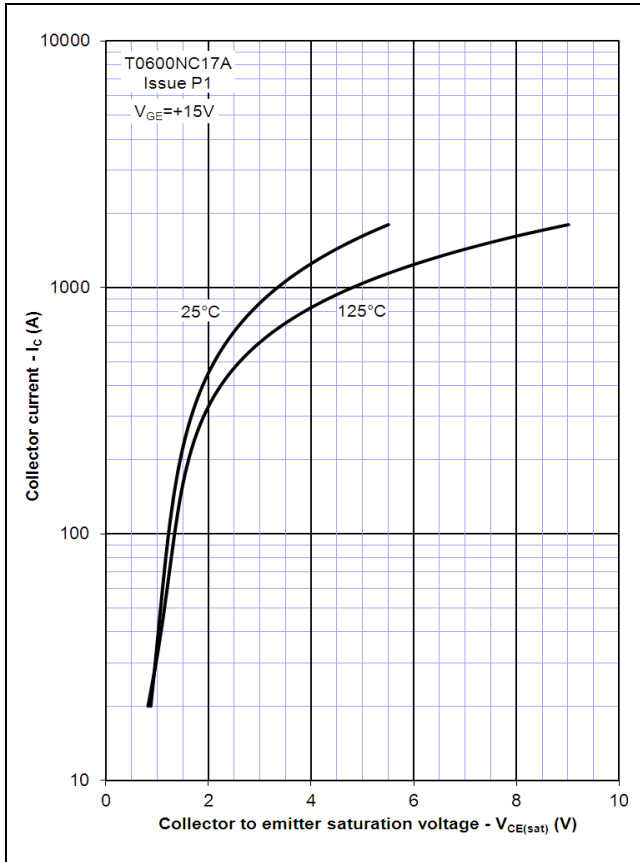


Figure 2 – Typical output characteristic

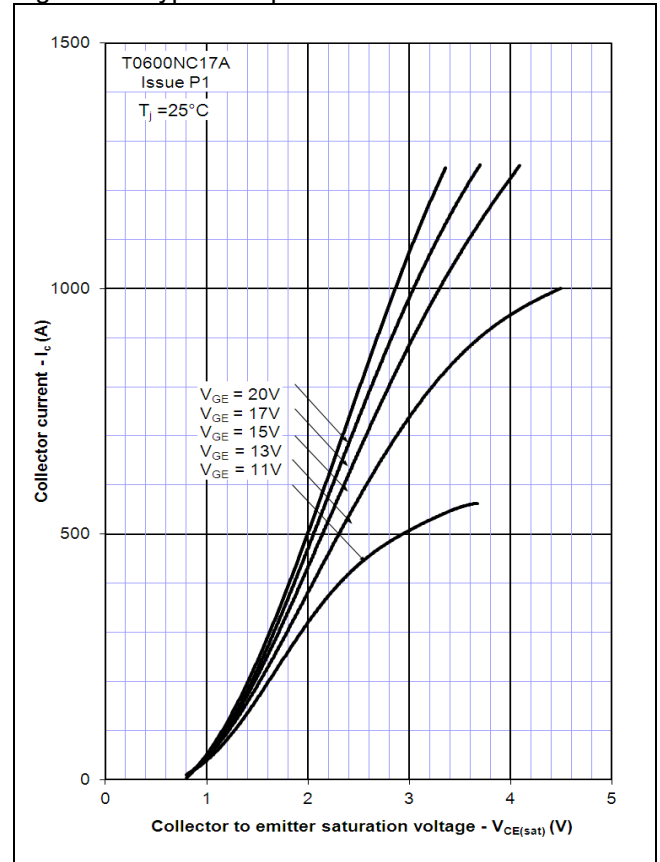


Figure 3 – Typical output characteristic

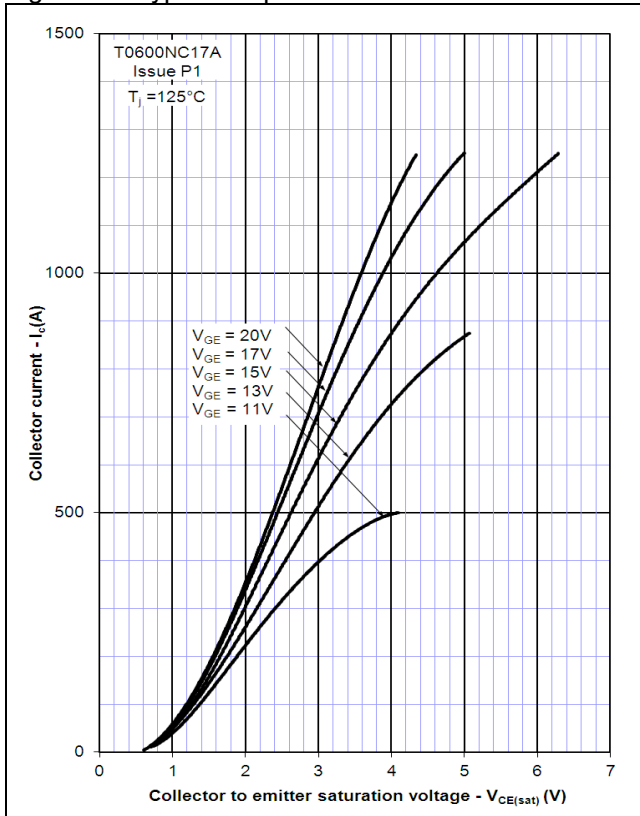


Figure 4 – Safe operating area (IGBT)

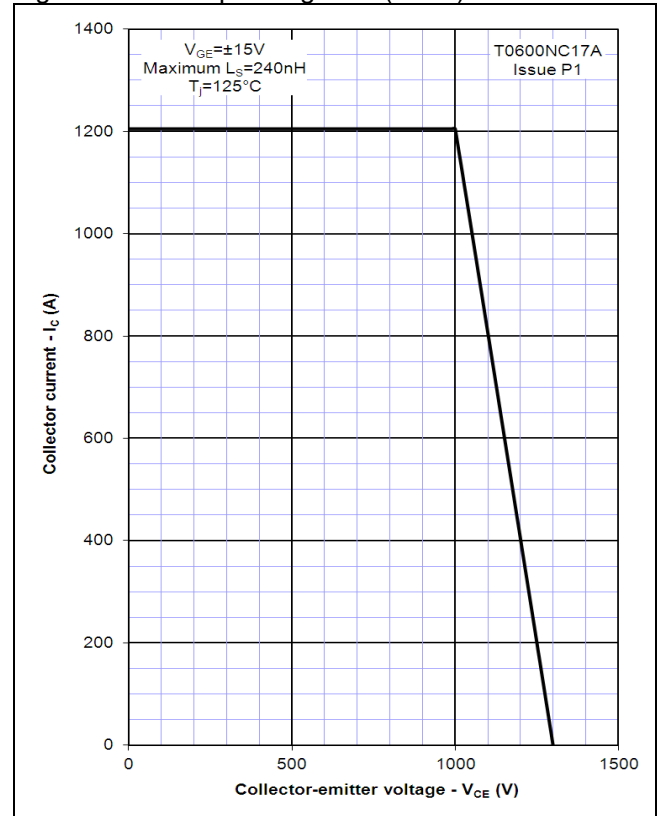


Figure 5 – Typical diode forward characteristics

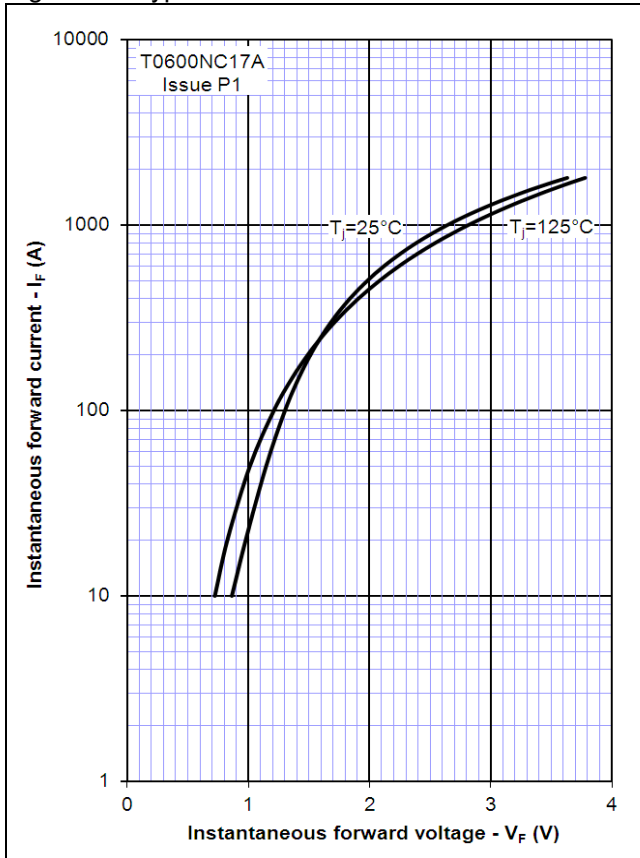


Figure 6 – Safe operating area (Diode)

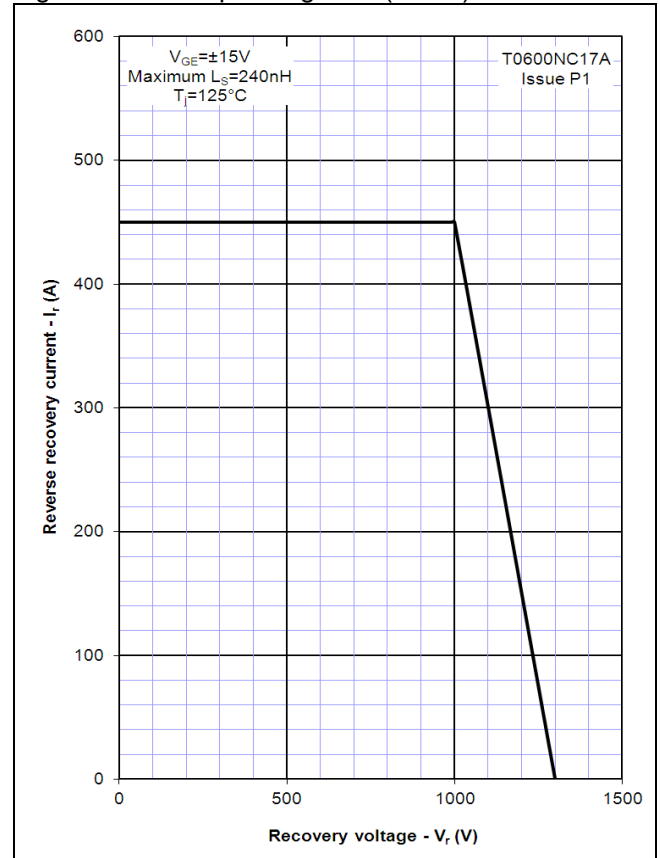


Figure 7 – Transient thermal impedance (IGBT)

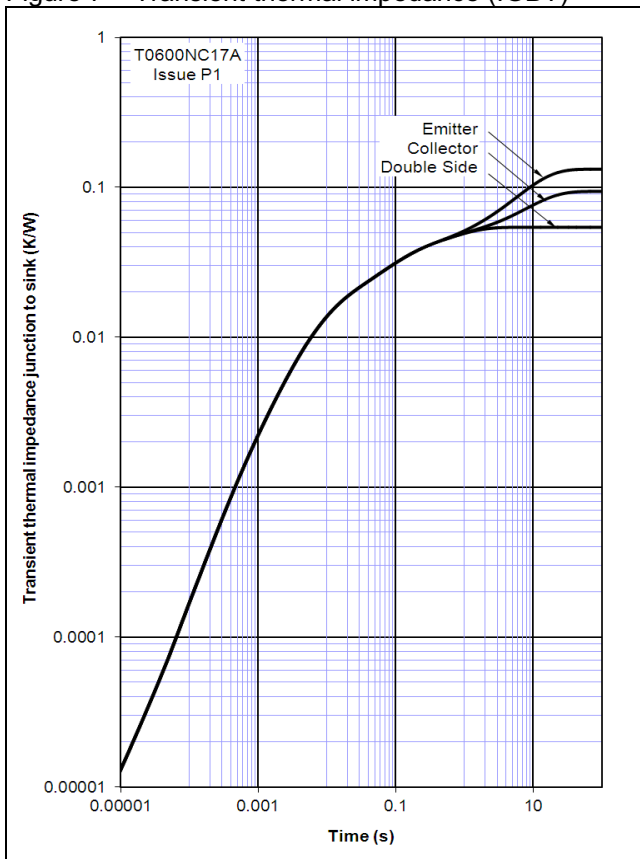
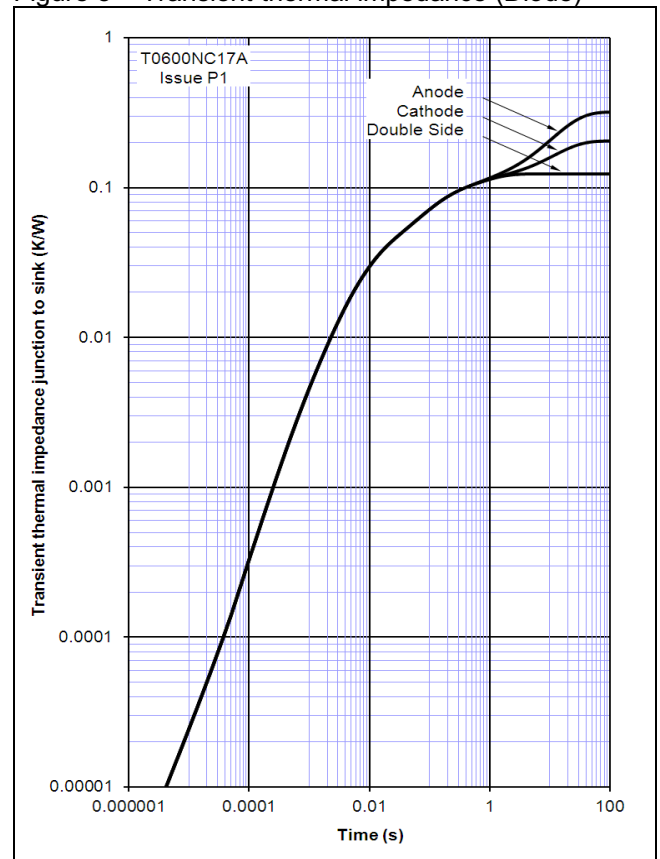
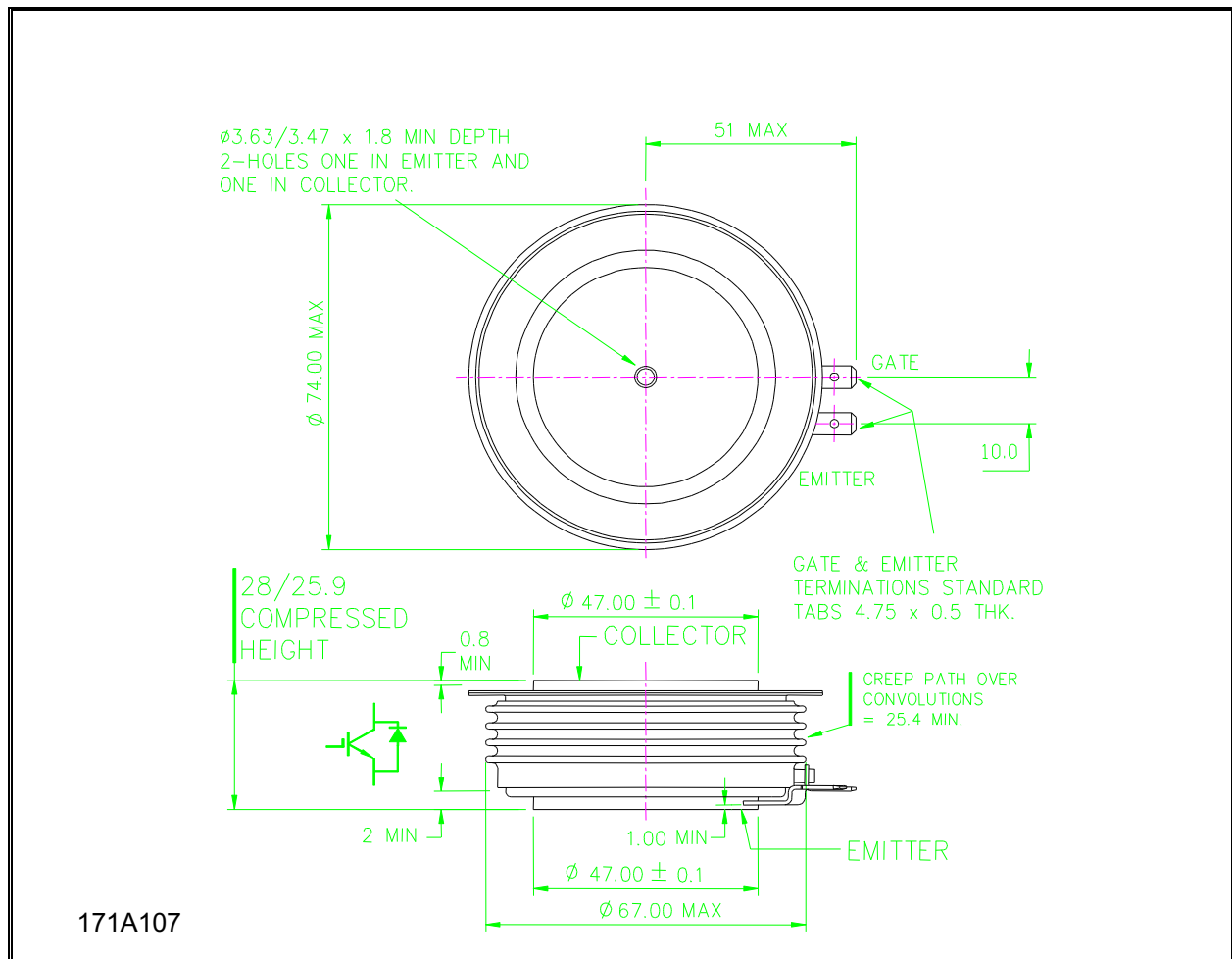


Figure 8 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION			
(Please quote 10 digit code as below)			
T0600	NC	17	A
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 17	Fixed format code

Typical order code: T0600NC17A ($V_{CES} = 1700V$)

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